

GAS FEEDING SYSTEM FOR CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF CONTROLLING THE SAME

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Abstract

The present invention relates to a gas feeding system, and more particularly, to a gas feeding system for chemical vapor deposition (CVD) reactor capable of improving the uniformity and quality of deposited film in the manufacture of semiconductor devices. The present invention also relates to a method of controlling the same which prevents the waste of reactant source. The gas feeding system of the present invention preferably comprises a plurality of reactant source supply apparatuses, each being connected to the reactor to supply different reactant sources therein discontinuously or sequentially. Each reactant source supply apparatus includes a pass valve to prevent the waste of non-use reactant sources.